ON Semiconductor®

# FDN360P

## Single P-Channel, PowerTrench® MOSFET

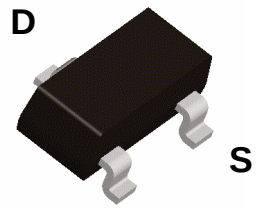
### General Description

This P-Channel Logic Level MOSFET is produced using ON Semiconductor advanced Power Trench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

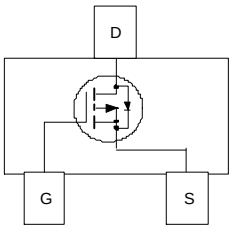
These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.

### Features

- –2 A, –30 V. $R_{DS(ON)}$ = 80 mΩ @ $V_{GS}$ = –10 V
  $R_{DS(ON)}$ = 125 mΩ @ $V_{GS}$ = –4.5 V
- Low gate charge (6.2 nC typical)
- High performance trench technology for extremely low $R_{DS(ON)}$ .
- High power version of industry Standard SOT-23 package. Identical pin-out to SOT-23 with 30% higher power handling capability.
- These Devices are Pb-Free and are RoHS Compliant




SuperSOT™-3




## Absolute Maximum Ratings

$T_A$=25°C unless otherwise noted

| Symbol | Parameter | | Ratings | Units |
|---|---|---|---|---|
| $V_{DSS}$ | Drain-Source Voltage | | –30 | V |
| $V_{GSS}$ | Gate-Source Voltage | | ±20 | V |
| $I_D$ | Drain Current – Continuous | (Note 1a) | –2 | A |
| | – Pulsed | | –10 | |
| $P_D$ | Power Dissipation for Single Operation | (Note 1a) | 0.5 | W |
| | | (Note 1b) | 0.46 | |
| $T_J$, $T_{STG}$ | Operating and Storage Junction Temperature Range | | –55 to +150 | °C |

## Thermal Characteristics

| | | | | |
|---|---|---|---|---|
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient | (Note 1a) | 250 | °C/W |
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case | (Note 1) | 75 | °C/W |

## Package Marking and Ordering Information

| Device Marking | Device | Reel Size | Tape width | Quantity |
|---|---|---|---|---|
| 360 | FDN360P | 7'' | 8mm | 3000 units |


November-2018, Rev. 7

Publication Order Number:
FDN360P /D

## Electrical Characteristics

$T_A$ = 25°C unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|---|---|---|---|---|---|---|
| **Off Characteristics** | | | | | | |
| $BV_{DSS}$ | Drain–Source Breakdown Voltage | $V_{GS}$ = 0 V, $I_D$ = –250 μA | –30 | | | V |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D$ = –250 μA, Referenced to 25°C | | –22 | | mV/°C |
| $I_{DSS}$ | Zero Gate Voltage Drain Current | $V_{DS}$ = –24V, $V_{GS}$ = 0 V | | | –1 | μA |
| | | $V_{DS}$ = –24V, $V_{GS}$ = 0 V, $T_J$=55°C | | | –10 | |
| $I_{GSSF}$ | Gate–Body Leakage, Forward | $V_{GS}$ = 20 V, $V_{DS}$ = 0 V | | | 100 | nA |
| $I_{GSSR}$ | Gate–Body Leakage, Reverse | $V_{GS}$ = –20 V, $V_{DS}$ = 0 V | | | –100 | nA |
| **On Characteristics** (Note 2) | | | | | | |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS}$ = $V_{GS}$, $I_D$ = –250 μA | –1 | –1.9 | –3 | V |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate Threshold Voltage Temperature Coefficient | $I_D$ = –250 μA, Referenced to 25°C | | 4 | | mV/°C |
| $R_{DS(on)}$ | Static Drain–Source On–Resistance | $V_{GS}$ = –10 V, $I_D$ = –2 A | | 63 | 80 | mΩ |
| | | $V_{GS}$ = –10 V, $I_D$ = –2 A, $T_J$=125°C | | 90 | 136 | |
| | | $V_{GS}$= –4.5 V, $I_D$ = –1.5A | | 100 | 125 | |
| $I_{D(on)}$ | On–State Drain Current | $V_{GS}$ = –10 V, $V_{DS}$ = –5 V | –10 | | | A |
| $g_{FS}$ | Forward Transconductance | $V_{DS}$ = –5 V, $I_D$ = –2 A | | 5 | | S |
| **Dynamic Characteristics** | | | | | | |
| $C_{iss}$ | Input Capacitance | $V_{DS}$ = –15 V, $V_{GS}$ = 0 V, f = 1.0 MHz | | 298 | | pF |
| $C_{oss}$ | Output Capacitance | | | 83 | | pF |
| $C_{rss}$ | Reverse Transfer Capacitance | | | 39 | | pF |
| **Switching Characteristics** (Note 2) | | | | | | |
| $t_{d(on)}$ | Turn–On Delay Time | $V_{DD}$ = –15 V, $I_D$ = –1 A, $V_{GS}$ = –10 V, $R_{GEN}$ = 6 Ω | | 6 | 12 | ns |
| $t_r$ | Turn–On Rise Time | | | 13 | 23 | ns |
| $t_{d(off)}$ | Turn–Off Delay Time | | | 11 | 20 | ns |
| $t_f$ | Turn–Off Fall Time | | | 6 | 12 | ns |
| $Q_g$ | Total Gate Charge | $V_{DS}$ = –15V, $I_D$ = –3.6 A, $V_{GS}$ = –10 V | | 6.2 | 9 | nC |
| $Q_{gs}$ | Gate–Source Charge | | | 1 | | nC |
| $Q_{gd}$ | Gate–Drain Charge | | | 1.2 | | nC |
| **Drain–Source Diode Characteristics and Maximum Ratings** | | | | | | |
| $I_S$ | Maximum Continuous Drain–Source Diode Forward Current | | | | –0.42 | A |
| $V_{SD}$ | Drain–Source Diode Forward Voltage | $V_{GS}$ = 0 V, $I_S$ = –0.42 A (Note 2) | | –0.8 | –1.2 | V |

**Notes:**

**1.** $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.

a) 250°C/W when mounted on a 0.02 in² pad of 2 oz. copper.

b) 270°C/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

**2.** Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

## Typical Characteristics

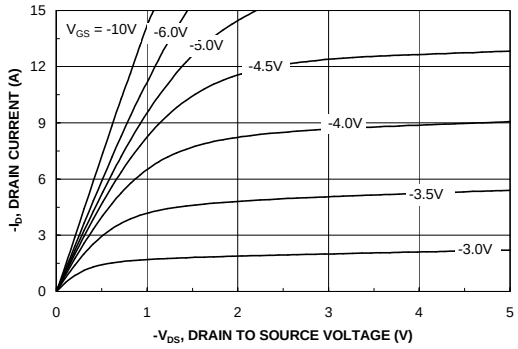



**Figure 1. On-Region Characteristics.**

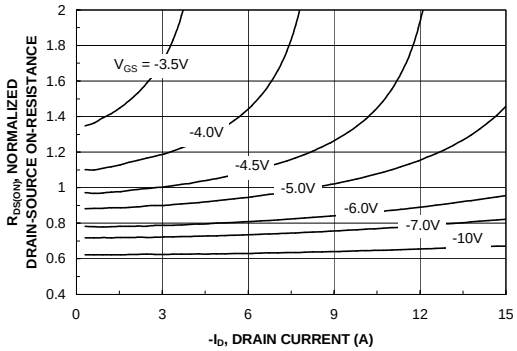



**Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.**

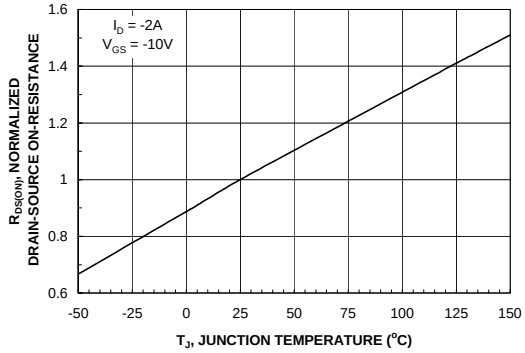



**Figure 3. On-Resistance Variation with Temperature.**

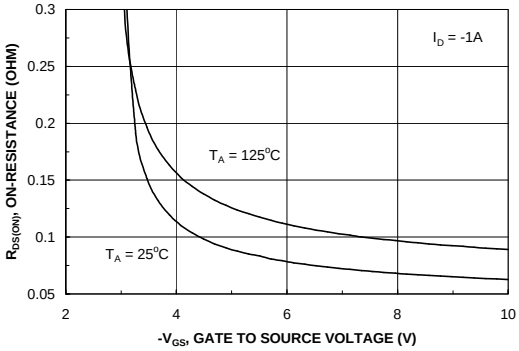



**Figure 4. On-Resistance Variation with Gate-to-Source Voltage.**

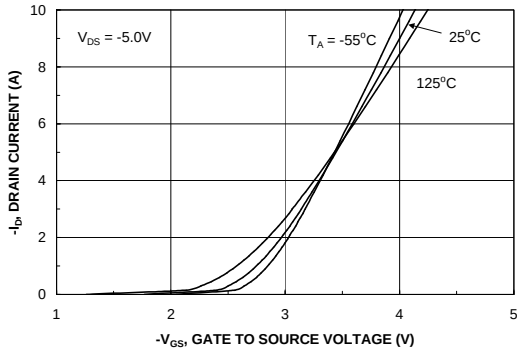



**Figure 5. Transfer Characteristics.**

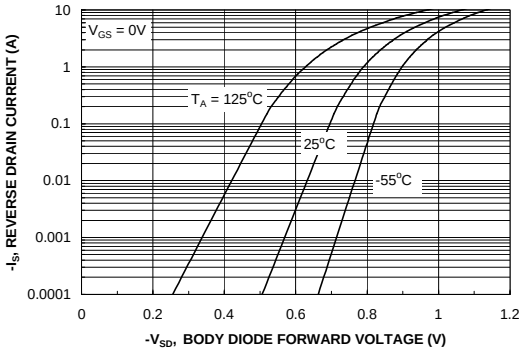



**Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.**

## Typical Characteristics

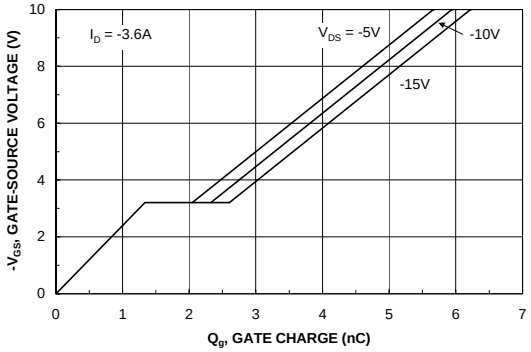



**Figure 7. Gate Charge Characteristics.**

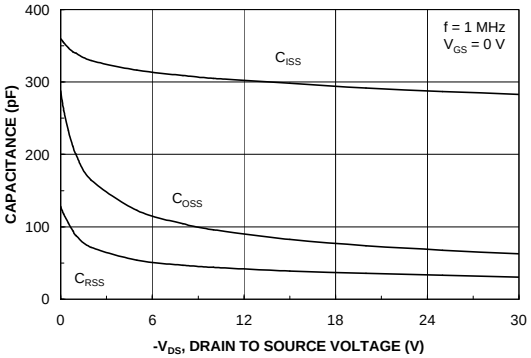



**Figure 8. Capacitance Characteristics.**

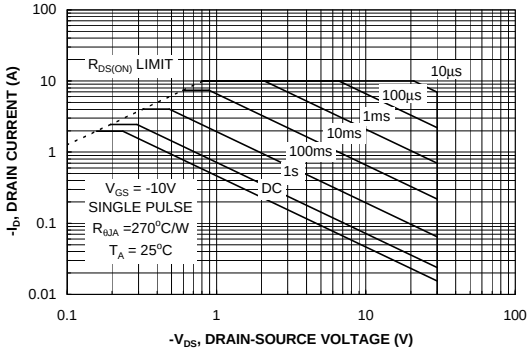



**Figure 9. Maximum Safe Operating Area.**

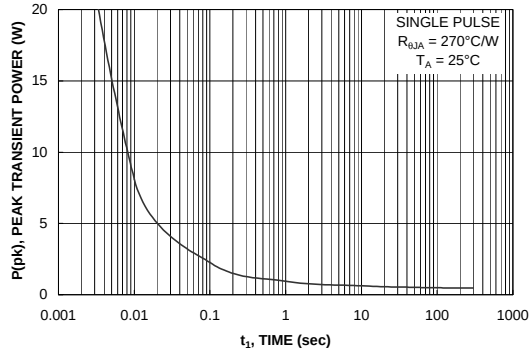



**Figure 10. Single Pulse Maximum Power Dissipation.**

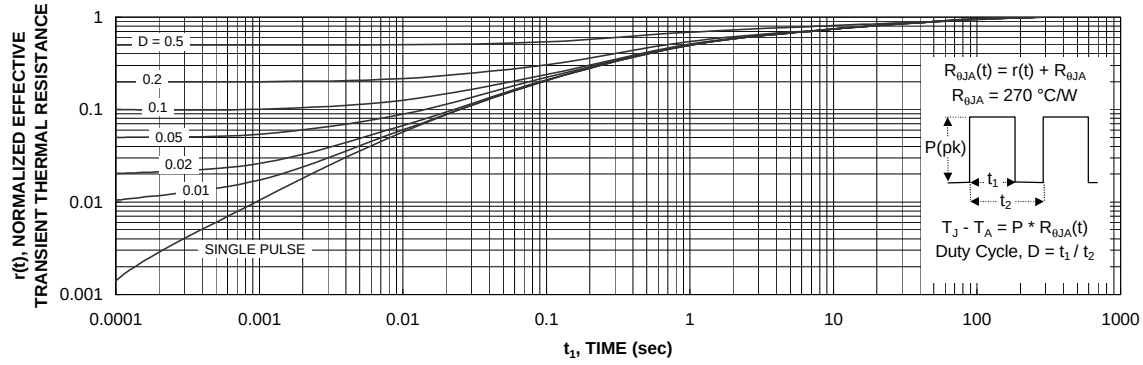
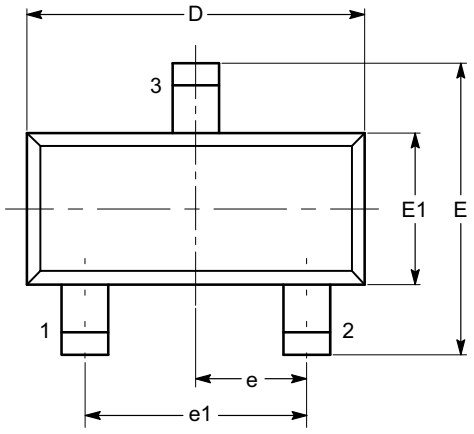



**Figure 11. Transient Thermal Response Curve.**

**Thermal characterization performed using the conditions described in Note 1b.**
**Transient thermal response will change depending on the circuit board design.**

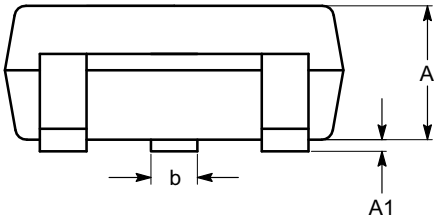
**SOT−23, 3 Lead**
CASE 527AG−01
ISSUE O

DATE 19 DEC 2008

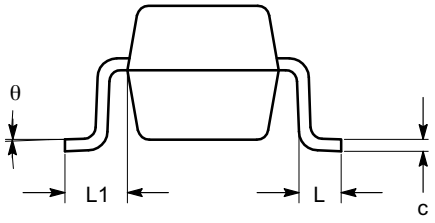



**TOP VIEW**

| SYMBOL | MIN | NOM | MAX |
|---|---|---|---|
| A | 0.89 | | 1.12 |
| A1 | 0.013 | | 0.10 |
| b | 0.37 | | 0.50 |
| c | 0.085 | | 0.18 |
| D | 2.80 | | 3.04 |
| E | 2.10 | | 2.64 |
| E1 | 1.20 | | 1.40 |
| e | 0.95 BSC | | |
| e1 | 1.90 BSC | | |
| L | 0.40 REF | | |
| L1 | 0.54 REF | | |
| θ | 0° | | 8° |




**SIDE VIEW**




**END VIEW**

**Notes:**
(1) All dimensions are in millimeters. Angles in degrees.
(2) Complies with JEDEC TO-236.

| ISSUE | REVISION | DATE |
|---|---|---|
| O | RELEASED FOR PRODUCTION FROM POD #SOT233−007−01 TO ON SEMICONDUCTOR. REQ. BY B. BERGMAN. | 19 DEC 2008 |
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